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(54) SEMICONDUCTOR DEVICE WITH ADJUSTMENT LAYERS AND METHOD FOR FABRICATING THE SAME

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(57)ABSTRACT

The present application discloses a semiconductor device with adjustment layers and a method for fabricating the semiconductor device with the adjustment layers. The semiconductor device includes a substrate, an interconnection structure positioned on the substrate, a contact positioned penetrating the interconnection structure, two adjustment layers positioned on sidewalls of the contact, a contact barrier layer positioned between the interconnection structure and the contact and between the substrate and the contact, wherein the two adjustment layers are positioned between the contact and the contact barrier layer. A bottom segment of the contact barrier layer is positioned between the substrate and the contact, and bottom most points of the two adjustment layers contact the bottom portion of the contact barrier layer.

